

IN THE CLAIMS:

Claim 1 has been amended herein. All of the pending claims 1 through 17 are presented below. This listing of claims will replace all prior versions and listings of claims in the application. Please enter these claims as amended.

Listing of Claims:

1. (Currently Amended) A semiconductor device having a portion thereof formed from a wafer of semiconductive material by a laser etching process comprising:
a substrate of semiconductive wafer material having a surface having a roughened surface thereon formed by a laser; and
resist on at least a portion of the surface of the substrate of semiconductive wafer material having a portion thereof removed by etching the resist from the surface of the substrate using a laser ~~forming a roughened surface on the surface of the substrate.~~
2. (Previously Presented) The semiconductor device according to claim 1, wherein the laser comprises a laser associated with an automolding system.
3. (Previously Presented) The semiconductor device according to claim 1, wherein the laser includes one of an Nd:YAG laser and an excimer laser.
4. (Previously Presented) The semiconductor device according to claim 1, wherein the substrate comprises a ball-grid-array substrate.
5. (Previously Presented) The semiconductor device according to claim 1, further comprising a vision system for detecting the resist.
6. (Previously Presented) The semiconductor device according to claim 5, wherein the vision system comprises:
a laser scanning system for detecting changes in a pattern of the substrate.

7. (Withdrawn) A method of enhancing the adhesion of a compound to a surface of a substrate comprising:
providing the substrate having the surface; and
roughening the surface of the substrate using a laser to remove material from the surface of the substrate.

8. (Withdrawn) The method according to claim 7, wherein roughening comprises removing contamination and foreign particles from the surface of the substrate.

9. (Withdrawn) An automolding system comprising:
providing a substrate having a surface;
preheating the substrate;
forming a resist layer;
baking the substrate; and
removing contaminants from the substrate using a laser.

10. (Withdrawn) The automolding system of claim 9, wherein the laser comprises one of an Nd:YAG laser and an excimer laser.

11. (Withdrawn) The automolding system of claim 9, further comprising:
placing the substrate in a mold; and
encapsulating the substrate.

12. (Previously Presented) A semiconductor device having a portion formed by a laser etching process on a substrate of semiconductive material having a surface comprising:
resist located on at least a portion of the surface having a portion thereof removed by etching the resist from the at least a portion of the surface of the substrate using a laser forming a roughened surface on the surface of the substrate of semiconductive material.

13. (Previously Presented) The semiconductor device according to claim 12, wherein the laser comprises a laser associated with an automolding system.

14. (Previously Presented) The semiconductor device according to claim 12, wherein the laser includes one of an Nd:YAG laser and an excimer laser.

15. (Previously Presented) The semiconductor device according to claim 12, wherein the substrate comprises a ball-grid-array substrate.

16. (Previously Presented) The semiconductor device according to claim 12, further comprising a vision system for detecting the resist.

17. (Previously Presented) The semiconductor device according to claim 16, wherein the vision system comprises: a laser scanning system for detecting changes in a pattern of the substrate.